

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
270V	100m Ω @10V	30A

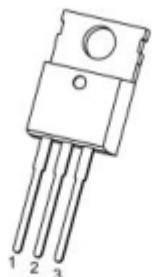
Feature

- Fast Switching
- Low Gate Charge and Rdson
- 100% Single Pulse avalanche energy Test

Application

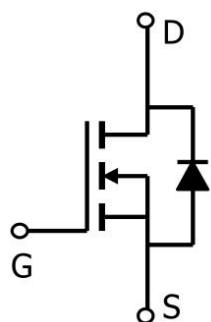
- DC-DC Converter
- Ideal for high-frequency switching and synchronous rectification

Package

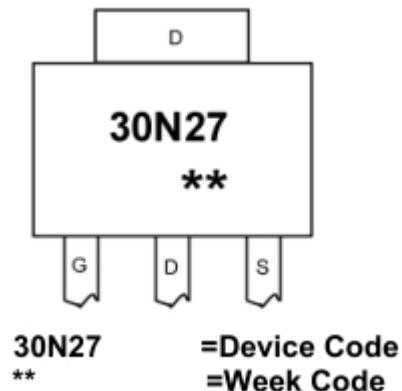


TO-220-3L-C(1:G 2:D 3:S)

Circuit diagram



Marking



Absolute maximum ratings

($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	270	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ¹ ($T_c=25^\circ\text{C}$)	I_D	30	A
Pulsed Drain Current ²	I_{DM}	120	A
Single Pulse Avalanche Energy ³	E_{AS}	949	mJ
Total Power Dissipation($T_c=25^\circ\text{C}$)	P_D	150	W
Thermal Resistance Junction-Case ¹	$R_{\theta JC}$	0.83	$^\circ\text{C}/\text{W}$
Storage Temperature Range	T_{STG}	-55 to 150	$^\circ\text{C}$
Operating Junction Temperature Range	T_J	-55 to 150	$^\circ\text{C}$

Electrical characteristics

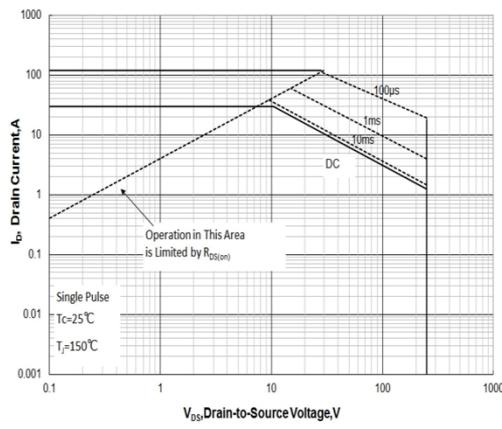
($T_A=25^\circ\text{C}$, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$\text{BV}_{(\text{BR})\text{DSS}}$	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$	270			V
Drain-Source Leakage Current	I_{DSS}	$V_{DS} = 200\text{V}, V_{GS} = 0\text{V}$			10	μA
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$			± 100	μA
Gate-Source Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	2	3	4	V
Static Drain-Source on-Resistance	$R_{DS(\text{on})}$	$V_{GS} = 10\text{V}, I_D = 15\text{A}$		100	120	$\text{m}\Omega$
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS} = 25\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$		1916		pF
Output Capacitance	C_{oss}			238		
Reverse Transfer Capacitance	C_{rss}			23		
Switching Characteristics						
Total Gate Charge	Q_g	$V_{DD} = 200\text{V}, V_{GS} = 10\text{V}, I_D = 30\text{A}$		36		nC
Gate-Source Charge	Q_{gs}			12		
Gate-Drain Charge	Q_{gd}			15		
Turn-on Delay Time	$T_{d(on)}$	$V_{GS} = 10\text{V}, V_{DD} = 125\text{V}, R_G = 10\Omega, I_D = 30\text{A}$		31		nS
Turn-on Rise Time	T_r			82		
Turn-off Delay Time	$T_{d(off)}$			49		
Turn-off Fall Time	T_f			20		

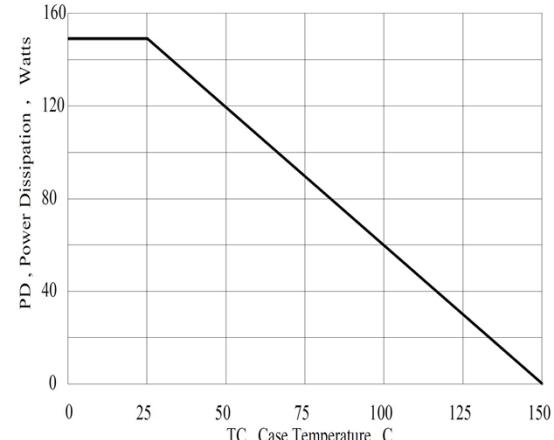
Note:

1. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
2. The data tested by pulsed , pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$
3. The E_{AS} data shows Max. rating . The test condition is $R_G = 30\Omega, L = 10\text{mH}$

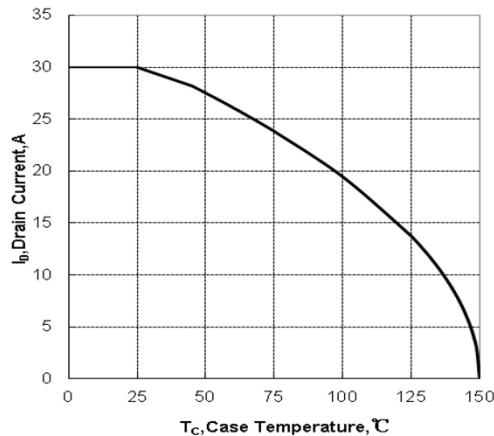
Typical Characteristics



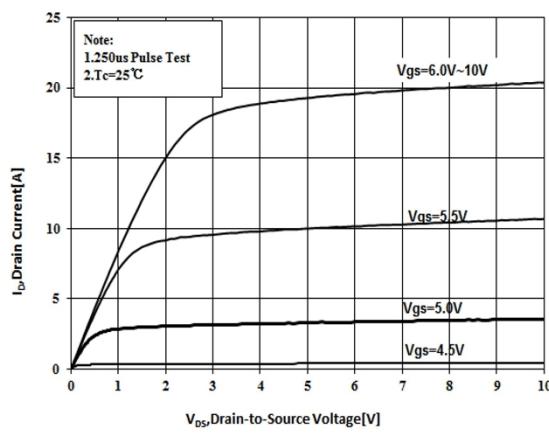
Maximum Forward Bias Safe Operating Area



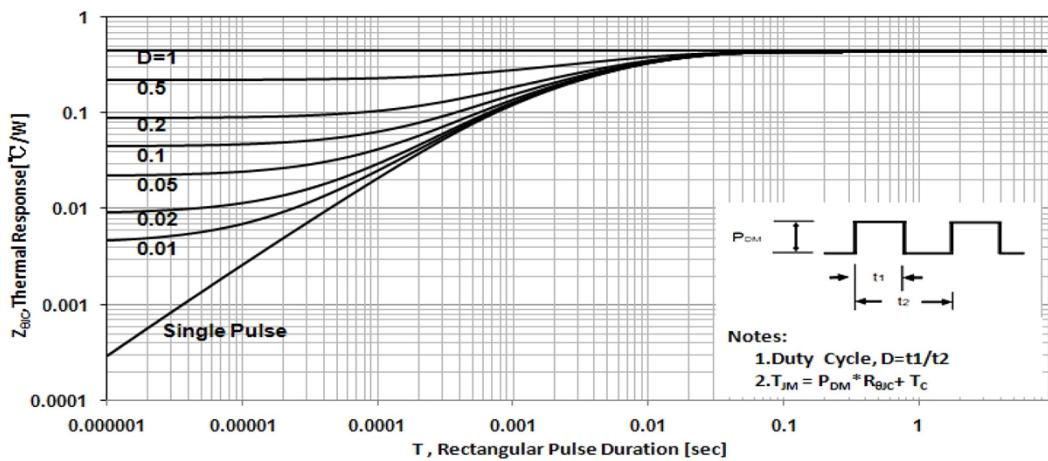
Maximum Power dissipation vs Case Temperature



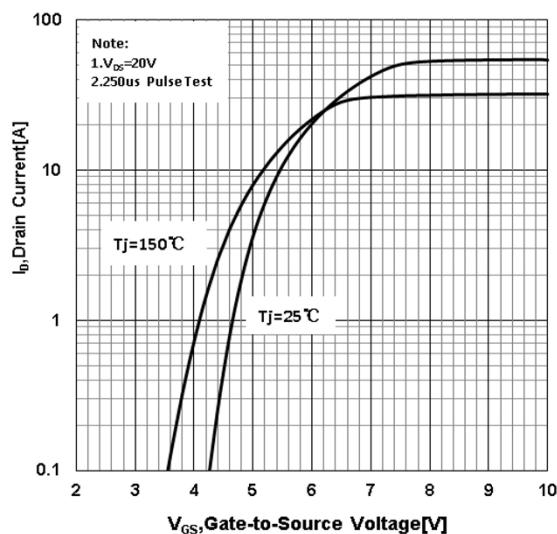
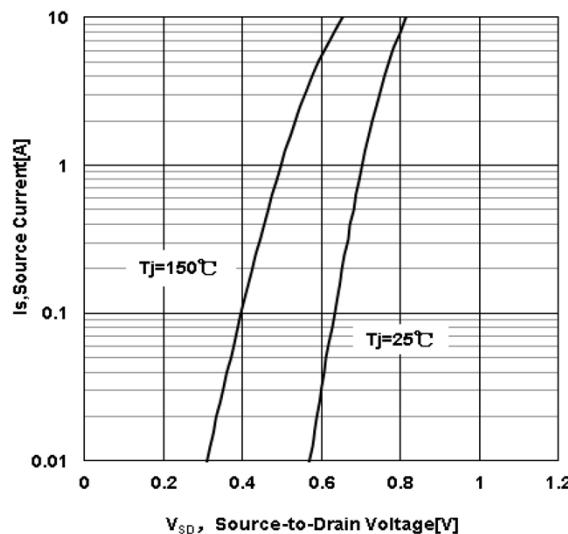
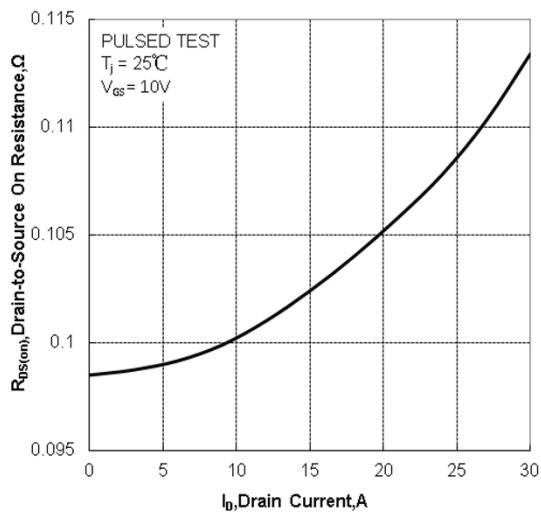
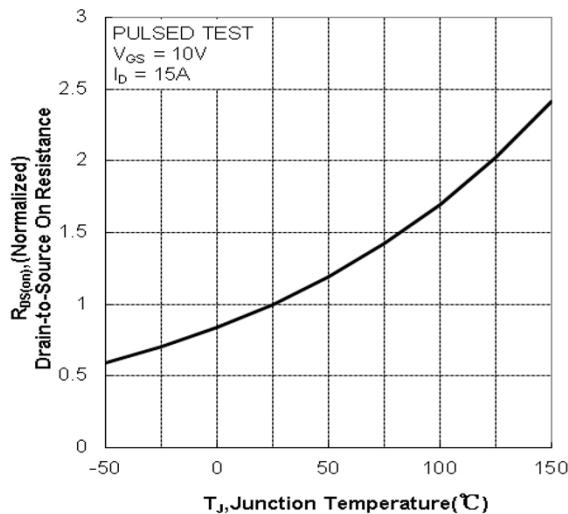
Maximum Continuous Drain Current vs Case Temperature

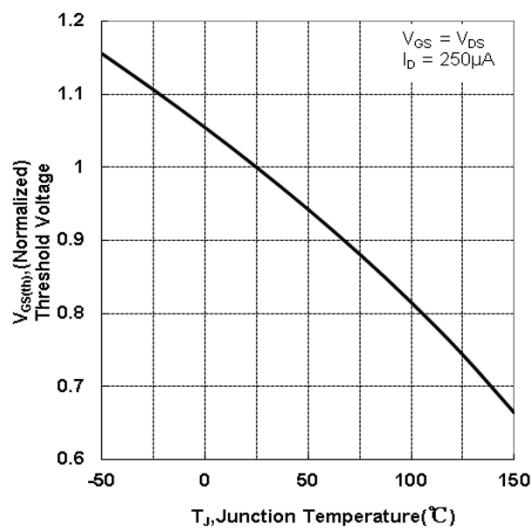
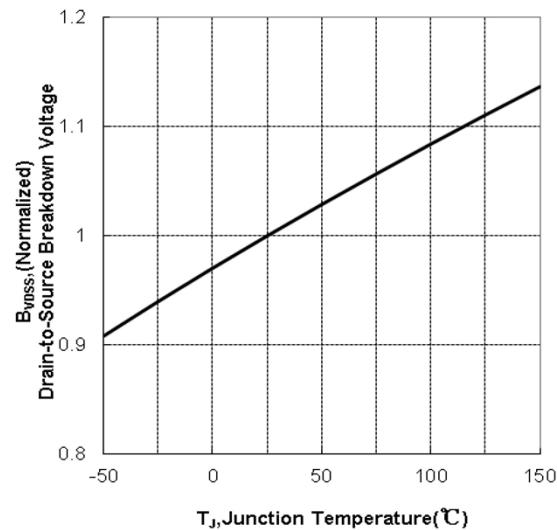
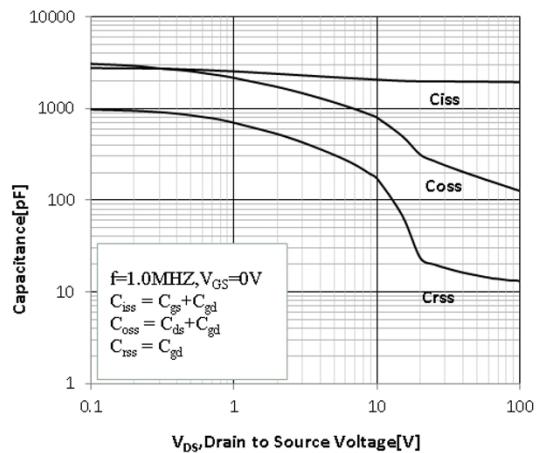
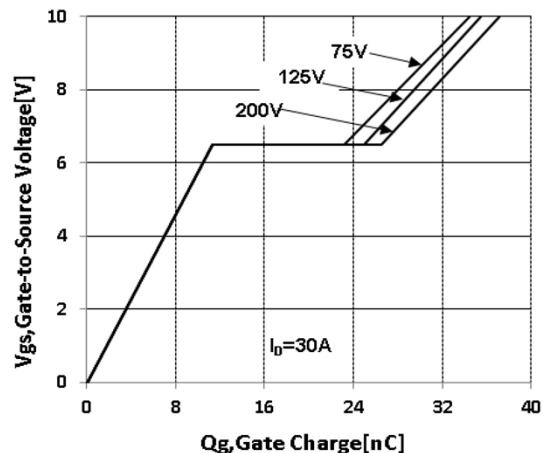


Typical Output Characteristics

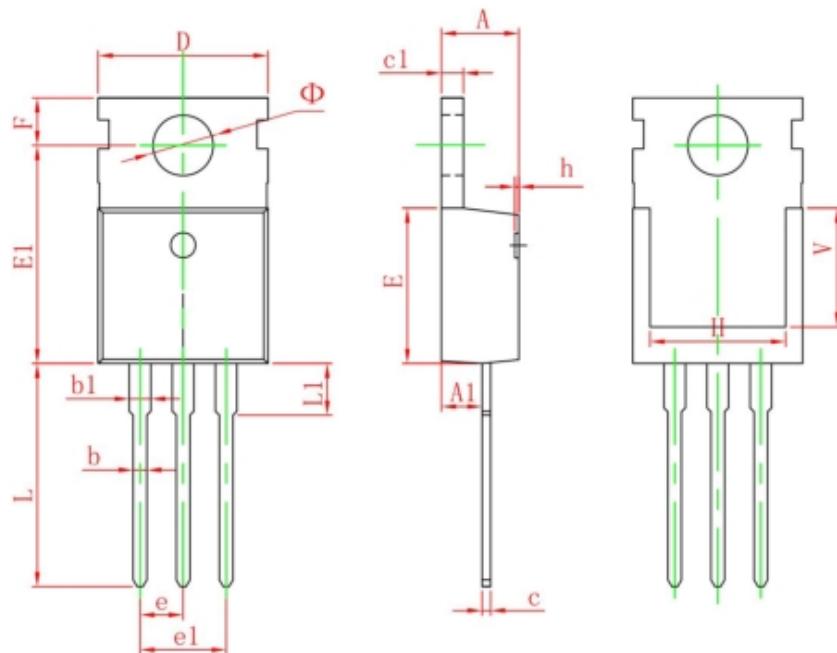


Maximum Effective Thermal Impedance , Junction to Case


Typical Transfer Characteristics

Typical Body Diode Transfer Characteristics

Typical Drain to Source ON Resistance vs Drain Current

Typical Drian to Source on Resistance vs Junction Temperature


Typical Threshold Voltage vs Junction Temperature

Typical Breakdown Voltage vs Junction Temperature

Typical Capacitance vs Drain to Source Voltage

Typical Gate Charge vs Gate to Source Voltage

TO-220-3L-C Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.400	4.600	0.173	0.181
A1	2.250	2.550	0.089	0.100
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.330	0.650	0.013	0.026
c1	1.200	1.400	0.047	0.055
D	9.910	10.250	0.390	0.404
E	8.950	9.750	0.352	0.384
E1	12.650	13.050	0.498	0.514
e	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204
F	2.650	2.950	0.104	0.116
H	7.900	8.100	0.311	0.319
h	0.000	0.300	0.000	0.012
L	12.900	13.400	0.508	0.528
L1	2.850	3.250	0.112	0.128
V	6.900 REF.		0.276 REF.	
Φ	3.400	3.800	0.134	0.150